

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Attorney Docket No.: VISH-8728.....

Inventor(s): Deva N. Pattanayak and Robert Xu

Serial No.:

Group Art Unit:

Filed: 12/02/03

Examiner:

Title: CLOSED CELL TRENCH METAL-OXIDE-SEMICONDUCTOR FIELD
EFFECT TRANSISTOR

Commissioner of Patents
P. O. Box 1450
Alexandria, VA 22313-1450

Sir:

Information Disclosure Statement Submitted Pursuant to 37 C.F.R. 1.97(b)

The citations referenced herein, copies attached, may be material to the examination of the above-identified application and are, therefore, submitted in compliance with the duty of disclosure as defined in 37 C.F.R. 1.56. The Examiner is requested to make these citations of official record in the application.

This Information Disclosure Statement submitted in accordance with 37 C.F.R. 1.97(b) is not to be construed as a representation that a search has been made, that additional items material to the examination of this application do not exist, or that any one or more of these citations constitute prior art under 35 U.S.C. 102.

The Examiner's attention is respectfully directed to the following U.S. Patents:

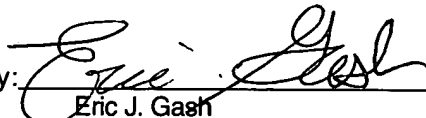
| <u>Pat. No.</u> | <u>Pat. Title</u> | <u>Grant Date</u> |
|-----------------|--|-------------------|
| 5,929,481 | HIGH DENSITY TRENCH DMOS TRANSISTOR WITH TRENCH BOTTOM IMPLANT | 07/27/99 |

Please direct all correspondence concerning the above-identified application to the following address:

WAGNER, MURABITO & HAO LLP
Two North Market Street, Third Floor
San Jose, California 95113
(408) 938-9060

Respectfully submitted,

Date: December 2, 2003

By: 
Eric J. Gash
Reg. No. 46,274

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE
Patent Application

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Form 1449

U.S. Patent Documents

| Examiner Initial | No. | Patent No. | Date | Patentee | Class | Sub-class | Filing Date |
|------------------|-----|------------|----------|----------------|-------|-----------|-------------|
| | A | 5,929,481 | 07/27/99 | Hshieh, et al. | 257 | 328 | 11/04/97 |
| | B | | | | | | |
| | C | | | | | | |
| | D | | | | | | |
| | E | | | | | | |
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| | K | | | | | | |

Foreign Patent or Published Foreign Patent Application

| Examiner Initial | No. | Document No. | Publication Date | Country or Patent Office | Class | Sub-class | Translation | |
|------------------|-----|--------------|------------------|--------------------------|-------|-----------|-------------|----|
| | | | | | | | Yes | No |
| | L | | | | | | | |
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| | O | | | | | | | |
| | P | | | | | | | |
| | Q | | | | | | | |

Other Documents

| Examiner Initial | | No. | Author, Title, Date, Place (e.g. Journal) of Publication |
|------------------|--|-----|--|
| | | R | |
| | | S | |
| | | T | |
| Examiner | | | Date Considered |

Examiner: Initial citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.